

ABSTRACT OF THE DISCLOSURE

A photomask having a trim mask, which includes a chrome mask placed at a position corresponding to a gate region and a phase shift mask placed at a position corresponding to a field poly region, and a method for manufacturing the same. In the case of using the trim mask, the margin of focal depth in the gate pattern region may be obtained, and simultaneously, the margin of focal depth in the field poly pattern region may be obtained. As a result, it is possible to reduce the length of a field poly pattern as well as the length of a gate pattern, and thus it is possible to reduce the size of a chip using the trim mask of the present invention. Moreover, the present invention facilitates performing optical proximity correction on the gate pattern region.